

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-23. (Cancelled).

24. (Currently amended) An apparatus ~~for etching a substrate material~~ comprising:
a chamber;
a support located within the chamber ~~to support the substrate material~~;
a quartz plate supported by the support;
a high frequency energy source;
a first gas supply providing a first gas, the first etchant gas comprising C_xF_y molecules, x and y being integers;
a first inlet for introducing the first gas into the chamber to form a first plasma gas when energized by the high frequency energy source;
a second gas supply providing a second gas, the second etchant gas comprising $SpFq$ molecules, p and q being integers; and
a second inlet for introducing the second gas into the chamber to form a second plasma gas when energized by the high frequency energy source;
wherein the first and second plasma gas are used to etch the quartz plate.

25. (Original) The apparatus of claim 24, further comprising a flow controller for controlling the amount of the first and second etchant gases entering the chamber.

26. (Currently amended) The apparatus of claim 24, wherein the first gas is comprises carbon fluoride and the second gas ~~is sulfur~~ comprises sulfur fluoride.